

FQP90N10V2/FQPF90N10V2

100V N-Channel MOSFET

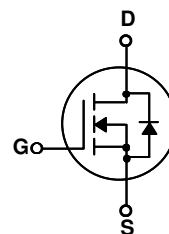
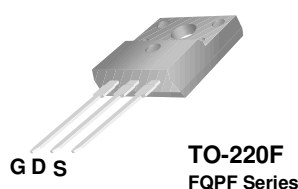
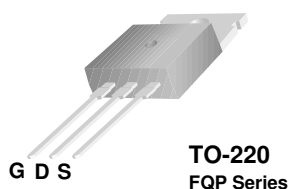
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for DC to DC converters, synchronous rectification, and other applications lowest Rds(on) is required.

Features

- 90 A, 100V, $R_{DS(on)} = 0.01\Omega @ V_{GS} = 10\text{ V}$
- Low gate charge (typical 147 nC)
- Low Crss (typical 300 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FQP90N10V2	FQPF90N10V2	Units
V _{DSS}	Drain-Source Voltage	100		V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	90	90 *	A
		68	68 *	A
I _{DM}	Drain Current - Pulsed (Note 1)	360	360 *	A
V _{GSS}	Gate-Source Voltage	± 30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	2430		mJ
I _{AR}	Avalanche Current (Note 1)	90		A
E _{AR}	Repetitive Avalanche Energy (Note 1)	25		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	250	83	W
		1.67	0.55	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175		°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP90N10V2	FQPF90N10V2	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	0.6	1.8	°C/W
R _{θJS}	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	100	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.1	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 80\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 45\text{ A}$	--	8.5	10	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 45\text{ A}$ (Note 4)	--	72	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	4730	6150	pF
C_{oss}	Output Capacitance		--	1180	1530	pF
C_{riss}	Reverse Transfer Capacitance		--	300	390	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{ V}, I_D = 90\text{ A},$ $R_G = 25\ \Omega$	--	52	114	ns
t_r	Turn-On Rise Time		--	492	994	ns
$t_{d(off)}$	Turn-Off Delay Time		--	304	618	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	355	720
Q_g	Total Gate Charge	$V_{DS} = 80\text{ V}, I_D = 90\text{ A},$ $V_{GS} = 10\text{ V}$	--	147	191	nC
Q_{gs}	Gate-Source Charge		--	28	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	60	--

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	90	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	360	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 90\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 90\text{ A},$	--	114	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	0.54	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 0.3\text{ mH}, I_{AS} = 90\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 90\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

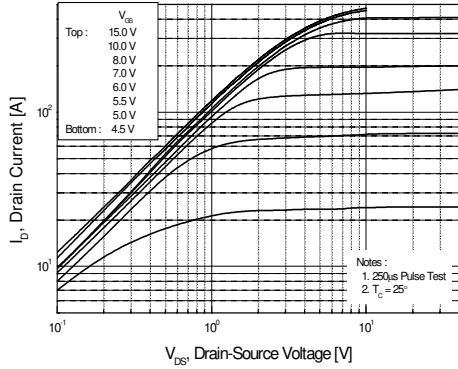


Figure 1. On-Region Characteristics

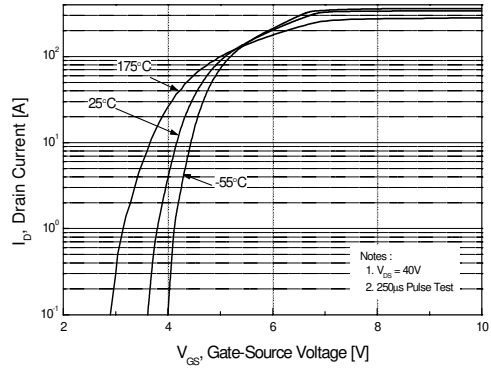


Figure 2. Transfer Characteristics

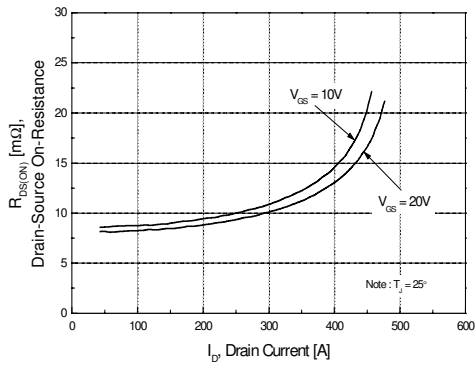


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

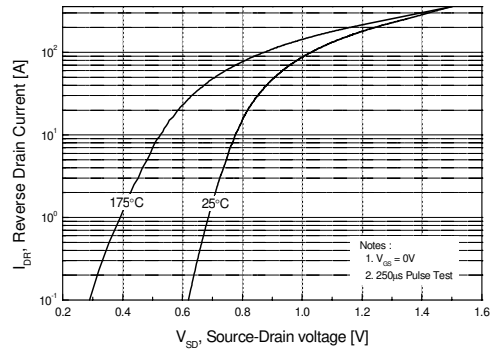


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

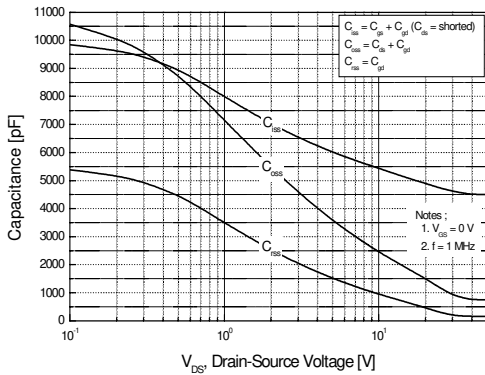


Figure 5. Capacitance Characteristics

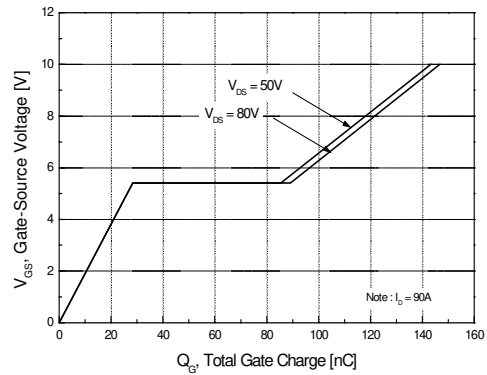


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

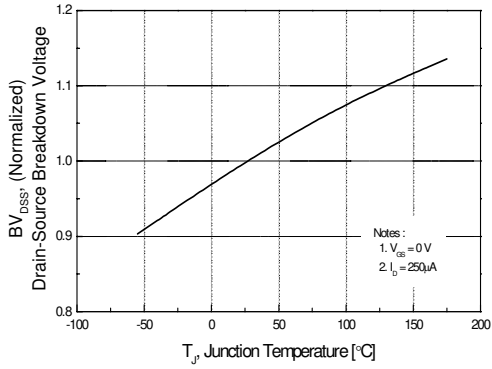


Figure 7. Breakdown Voltage Variation vs Temperature

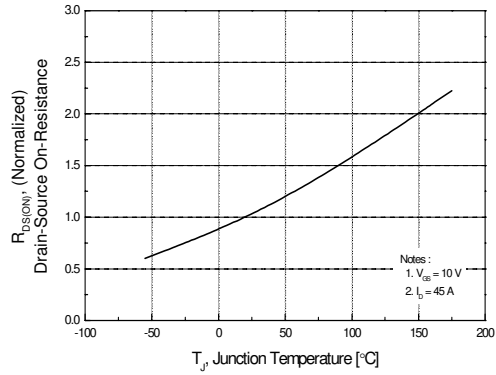


Figure 8. On-Resistance Variation vs Temperature

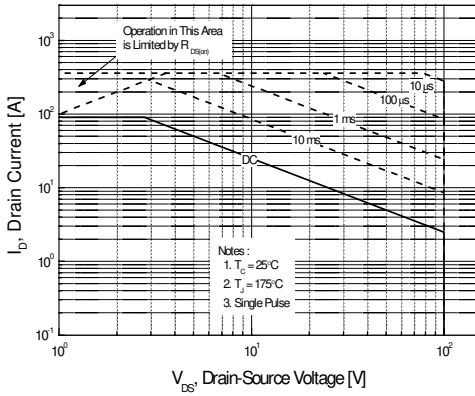


Figure 9-1. Maximum Safe Operating Area for FQP90N10V2

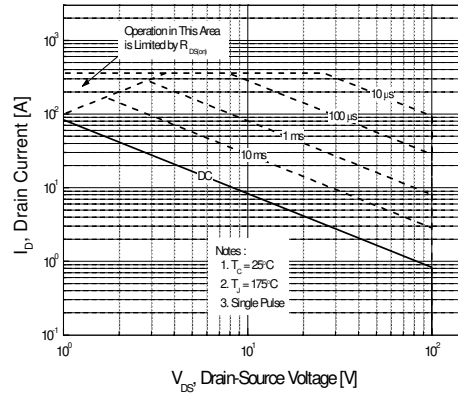


Figure 9-2. Maximum Safe Operating Area for FQP90N10V2

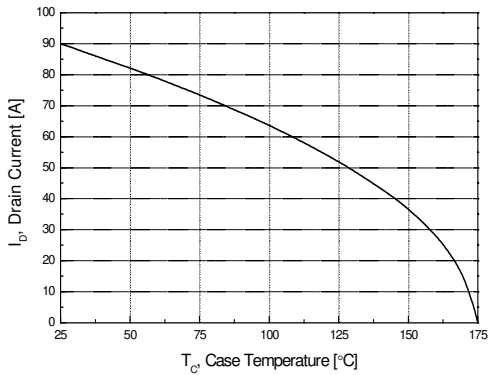


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

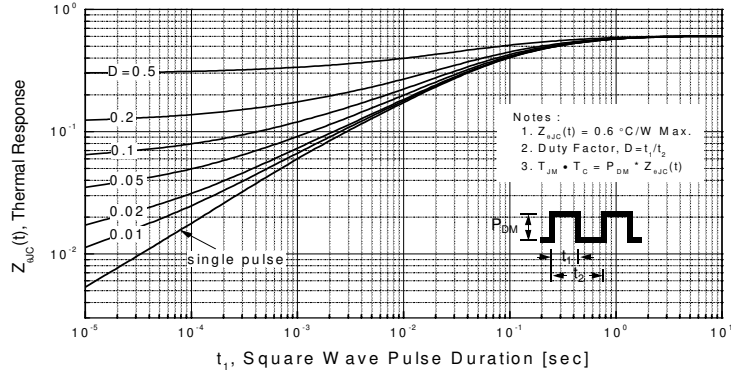


Figure 11-1. Transient Thermal Response Curve for FQP90N10V2

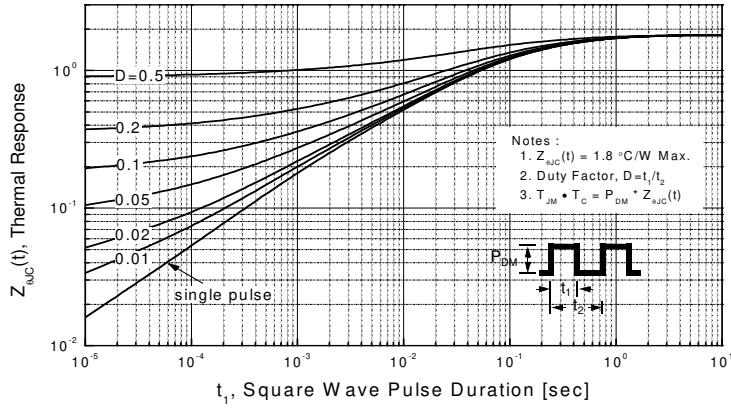
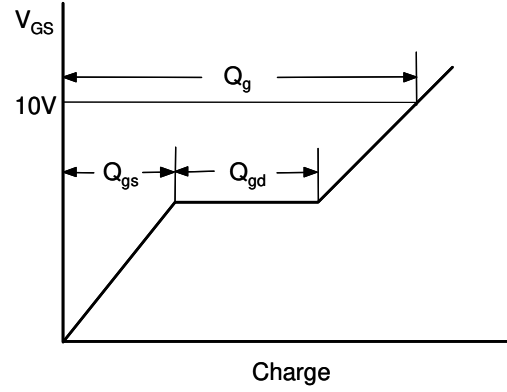
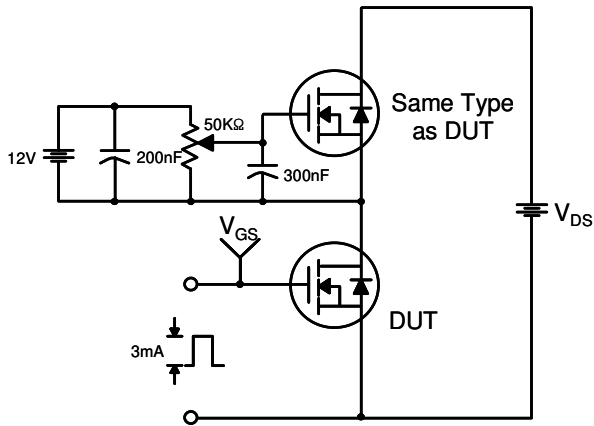
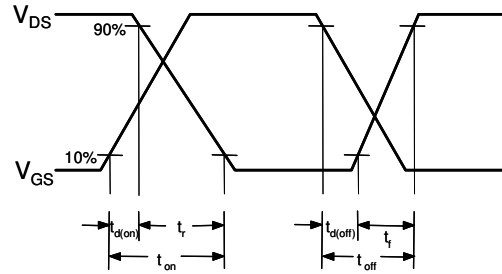
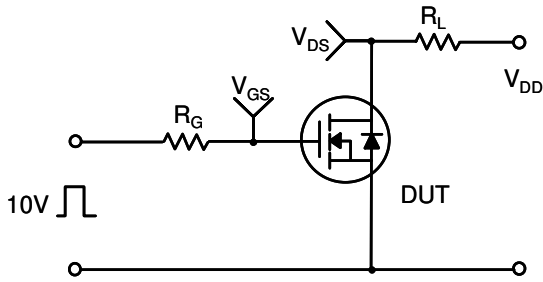


Figure 11-2. Transient Thermal Response Curve for FQPF90N10V2

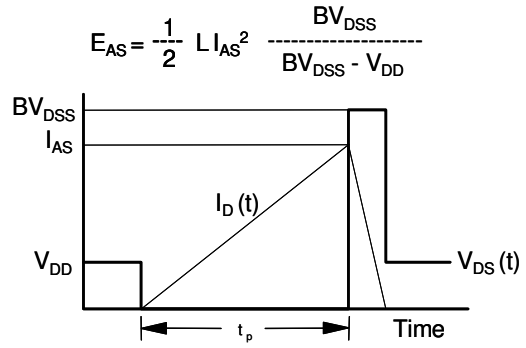
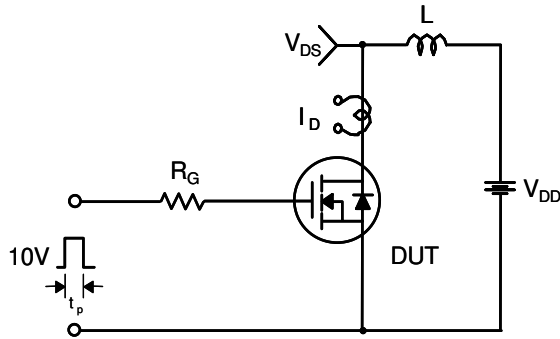
Gate Charge Test Circuit & Waveform



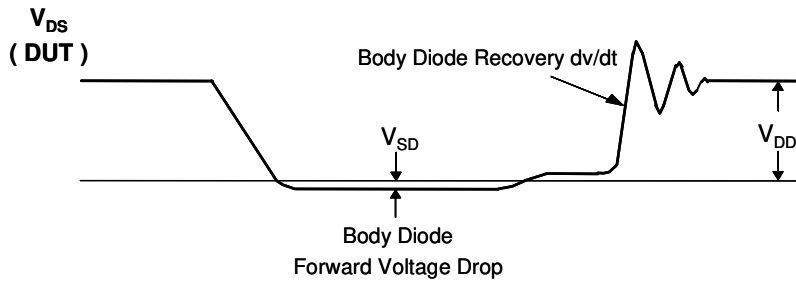
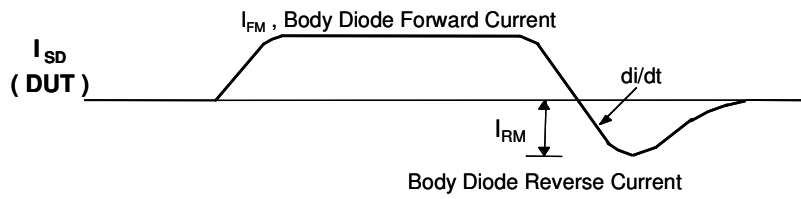
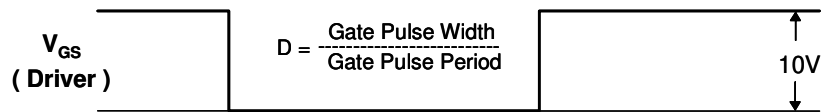
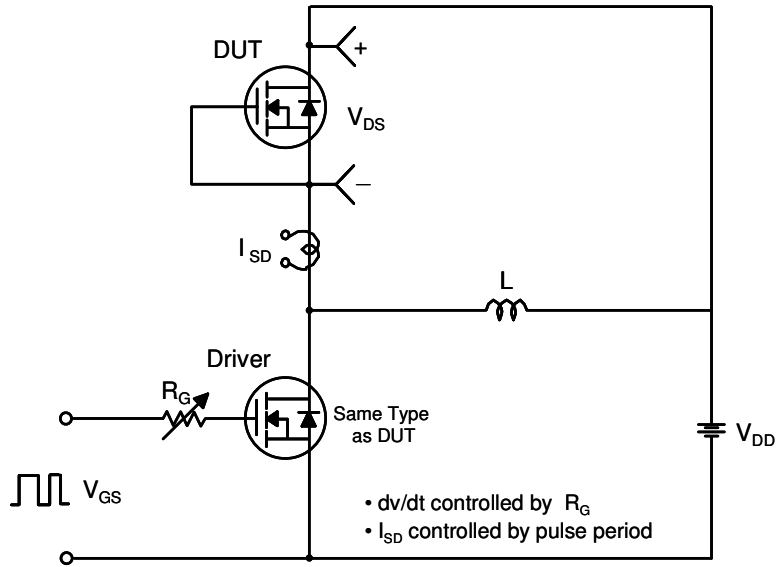
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

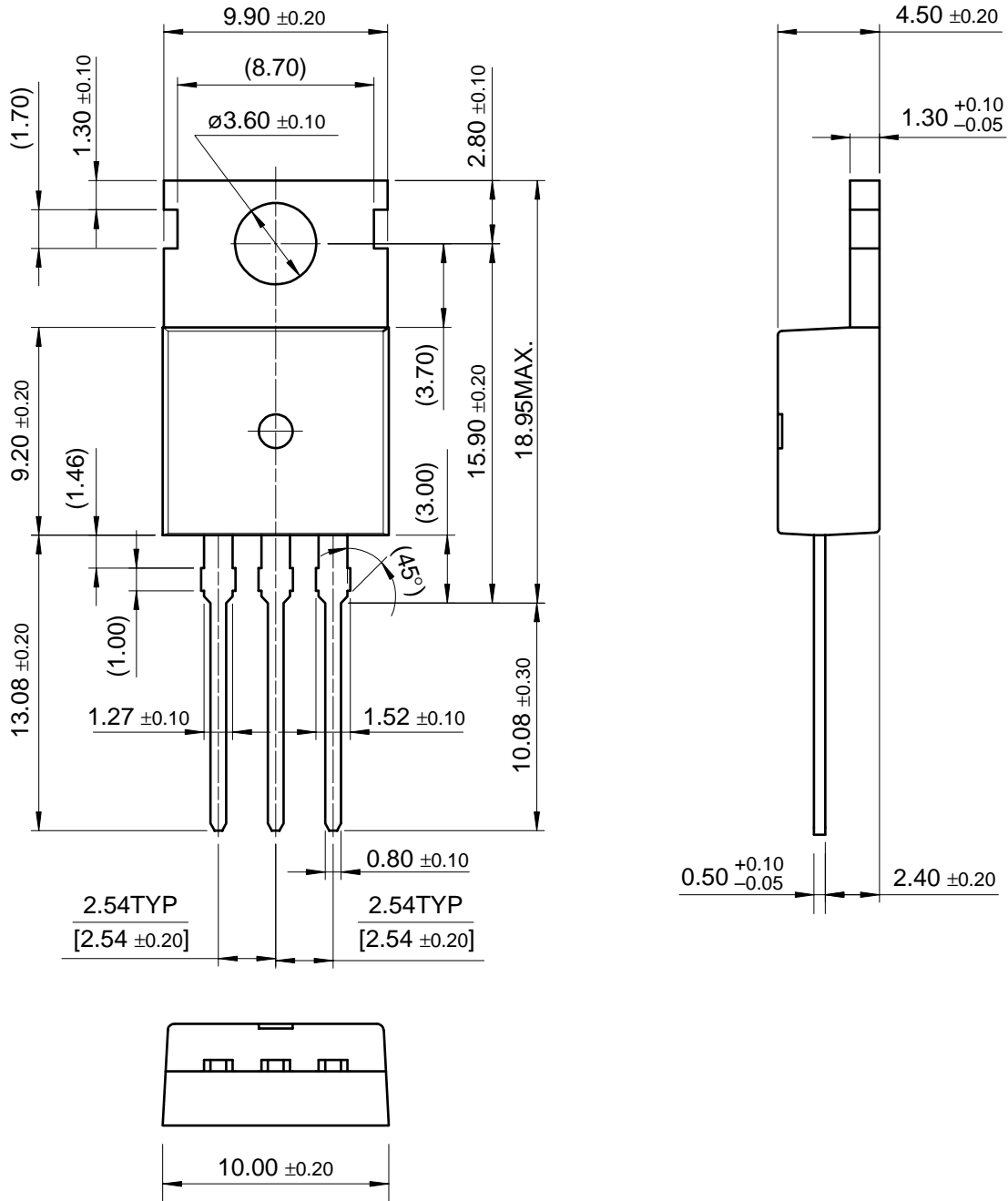


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-220

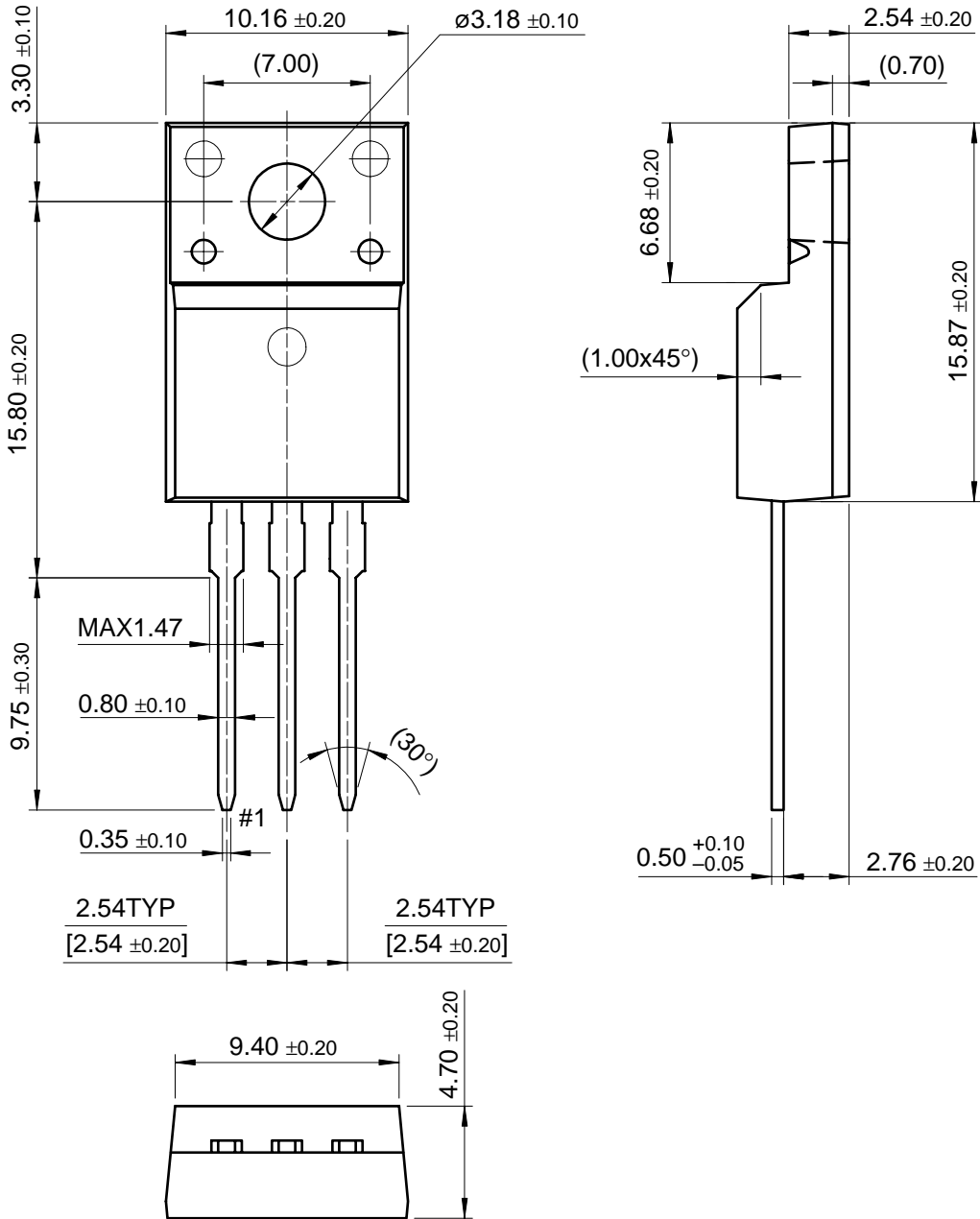


FQP90N10V2/FQP90N10V2

Dimensions in Millimeters

Package Dimensions (Continued)

TO-220F



Note: PKG backside isolation voltage : 4000V

Dimensions in Millimeters

FQP90N10V2/FQP90N10V2

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